Si844x/5x QSOP



FOUR AND FIVE-CHANNEL DIGITAL ISOLATORS

Up to 1000 V_{RMS} isolation

• 1.5 ns pulse width distortion

0.5 ns channel-channel skew

• 2 ns propagation delay skew

• 6 ns minimum pulse width Transient Immunity 25 kV/µs

Wide temperature range

• -40 to 125 °C at 150 Mbps

Precise timing (typical)

<10 ns worst case

Features

- High-speed operation • DC to 150 Mbps
- No start-up initialization required
- Wide Operating Supply Voltage: 2.70-5.5 V
- Ultra low power (typical) 5 V Operation:
 - < 1.6 mA per channel at 1 Mbps</p>
 - < 6 mA per channel at 100 Mbps
 - 2.70 V Operation:
 - < 1.4 mA per channel at 1 Mbps
 RoHS-compliant packages
 - < 4 mA per channel at 100 Mbps
- High electromagnetic immunity

Applications

- Industrial automation systems
- Isolated switch mode supplies
- Isolated ADC, DAC

Safety Regulatory Approvals

- UL 1577 recognized
 - Up to 1000 V_{RMS} for 1 minute
- CSA component notice 5A approval

Description

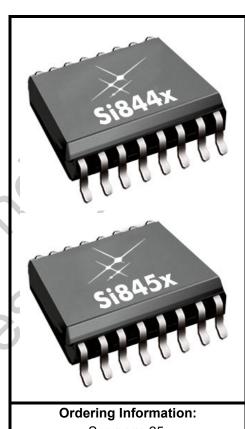
Skyworks Solutions' family of ultra-low-power digital isolators are CMOS devices offering substantial data rate, propagation delay, power, size, reliability, and external BOM advantages when compared to legacy isolation technologies. The operating parameters of these products remain stable across wide temperature ranges throughout their service life. For ease of design, only VDD bypass capacitors are required.

Data rates up to 150 Mbps are supported, and all devices achieve worst-case propagation delays of less than 10 ns. These devices are available in a 16-pin QSOP package.

Motor control

QSOP-16

- Power inverters
- - VDE certification conformity IEC 60747-5-2
 - (VDE0884 Part 2)



See page 25.

Communications systems



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1. Electrical Specifications

Table 1. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Ambient Operating Temperature*	T _A	150 Mbps, 15 pF, 5 V	-40	25	125	°C
Supply Voltage	V _{DD1}		2.70	—	5.5	V
	V _{DD2}		2.70	—	5.5	V
*Note: The maximum ambient temperature and supply voltage.	e is depende	nt on data frequency, outp	out loading, r	number of op	erating char	nnels,

Table 2. Absolute Maximum Ratings¹

Parameter	Symbol	Min	Тур	Max	Unit
Storage Temperature ²	T _{STG}	-65	5	150	°C
Ambient Temperature Under Bias	TA	-40	$\left(+ \right)$	125	°C
Supply Voltage	V _{DD1} , V _{DD2}	-0.5	—	6.0	V
Input Voltage	VI	-0.5	2 –	V _{DD} + 0.5	V
Output Voltage	Vo	-0.5	_	V _{DD} + 0.5	V
Output Current Drive Channel	lo	/ _	_	10	mA
Lead Solder Temperature (10 s)		—	_	260	°C
Maximum Isolation (Input to Output) (1 sec) QSOP-16			_	1000	V _{RMS}
Notos:					

Notes:

1. Permanent device damage may occur if the absolute maximum ratings are exceeded. Functional operation should be restricted to conditions as specified in the operational sections of this data sheet.

2. VDE certifies storage temperature from -40 to 150 °C.

Table 3. Electrical Characteristics

 $(V_{DD1} = 5 V \pm 10\%, V_{DD2} = 5 V \pm 10\%, T_A = -40 \text{ to } 125 \text{ °C})$

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
High Level Input Voltage	V _{IH}		2.0	—		V
Low Level Input Voltage	V _{IL}		—	_	0.8	V
High Level Output Voltage	V _{OH}	loh = –4 mA	$V_{DD1}, V_{DD2} - 0.4$	4.8		V
Low Level Output Voltage	V _{OL}	lol = 4 mA	_	0.2	0.4	V
Input Leakage Current	١L			—	±10	μA
Output Impedance ¹	Z _O		_	85	_	Ω
Enable Input High Current	I _{ENH}	V _{ENx} = V _{IH}	- 0	2.0	_	μA
Enable Input Low Current	I _{ENL}	$V_{ENx} = V_{IL}$	_	2.0	_	μA
		Current (All inputs	0 V or at Supply)			
Si8455Bx						
V _{DD1}		All inputs 0 DC		1.6	2.4	
V _{DD2}		All inputs 0 DC		2.9	4.4	mA
V _{DD1}		All inputs 1 DC		7.0	10.5	
V _{DD2}		All inputs 1 DC		3.1	4.7	
				5.1	4.7	
Si8442Bx			6			
V _{DD1}		All inputs 0 DC		2.3	3.5	
V _{DD2}		All inputs 0 DC		2.3	3.5	mA
V _{DD1}		All inputs 1 DC	—	4.5	6.8	
V _{DD2}		All inputs 1 DC	-	4.5	6.8	
1 Mbps Supply C	urrent (All in	nputs = 500 kHz squ	are wave, CI = 15 pł	= on all outp	outs)	
Si8455Bx						
V _{DD1}			—	4.3	6.5	mA
V _{DD2}			—	3.5	5.3	
Si8442Bx						
V _{DD1}			_	3.6	5.4	mA
V _{DD2}		Ψ.	_	3.6	5.4	
	Current (All	inputs = 5 MHz squ	are wave, CI = 15 pF	on all outp	outs)	
Si8455Bx				-		
V _{DD1}			_	4.3	6.5	mA
V _{DD2}				4.8	6.7	
Si8442Bx				-		
				4.2	5.9	mA
V _{DD1}				4.2	5.9 5.9	
V _{DD2}			_	4.2	5.9	
Notes:	,	, ,		00/		
1. The nominal output impedat						
the value of the on-chip series						
where transmission line effe	cts will be a t	actor, output pins shot	no pe appropriately ter	minated with	controlled	

2. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

3. Start-up time is the time period from the application of power to valid data at the output.

Table 3. Electrical Characteristics (Continued)

 $(V_{DD1} = 5 V \pm 10\%, V_{DD2} = 5 V \pm 10\%, T_A = -40 \text{ to } 125 \text{ °C})$

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
100 Mbps Supply	Current (All	inputs = 50 MHz squ	are wave, CI = 15	pF on all ou	tputs)	I
Si8455Bx						
V _{DD1}			_	4.6	6.9	mA
V _{DD2}			—	24	30	
Si8442Bx						
V _{DD1}			—	11.8	14.8	mA
V _{DD2}			—	11.8	14.8	
		Timing Characteris	stics			
Si845xAx, Si8442Bx			NC NC			
Maximum Data Rate			0	—	1.0	Mbps
Minimum Pulse Width			A		250	ns
Propagation Delay	t _{PHL} , t _{PLH}	See Figure 2	<u> </u>		35	ns
Pulse Width Distortion	PWD	See Figure 2	<u> </u>		25	ns
t _{PLH} - t _{PHL}						
Propagation Delay Skew ²	t _{PSK(P-P)}		-	\mathbf{D} –	40	ns
Channel-Channel Skew	t _{PSK}			_	35	ns
Si845xBx, Si8442Bx						
Maximum Data Rate			0	—	150	Mbps
Minimum Pulse Width			—	—	6.0	ns
Propagation Delay	t _{PHL} , t _{PLH}	See Figure 2	3.0	6.0	9.5	ns
Pulse Width Distortion	PWD	See Figure 2		1.5	2.5	ns
t _{PLH} - t _{PHL}						
Propagation Delay Skew ²	t _{PSK(P-P)}		—	2.0	3.0	ns
Channel-Channel Skew	t _{PSK}		—	0.5	1.8	ns
All Models						
Output Rise Time	tr	C _L = 15 pF	—	3.8	5.0	ns
	(\cdot)	See Figure 2				
Output Fall Time	t _f	C _L = 15 pF	—	2.8	3.7	ns
	·	See Figure 2				
Common Mode Transient Immunity	CMTI	$V_{I} = V_{DD} \text{ or } 0 \text{ V}$	—	25	—	kV/µs
Enable to Data Valid	t _{en1}	See Figure 1	—	5.0	8.0	ns
Enable to Data Tri-State	t _{en2}	See Figure 1	—	7.0	9.2	ns
Start-up Time ³	t _{SU}		_	15	40	μs

Notes:

 The nominal output impedance of an isolator driver channel is approximately 85 Ω, ±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces.

2. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

3. Start-up time is the time period from the application of power to valid data at the output.

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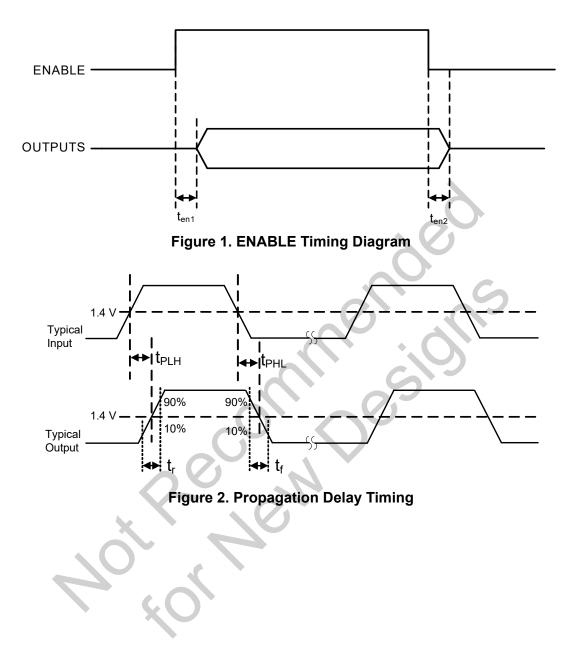


Table 4. Electrical Characteristics

 $(V_{DD1} = 3.3 \text{ V}\pm 10\%, V_{DD2} = 3.3 \text{ V}\pm 10\%, T_A = -40 \text{ to } 125 \text{ °C})$

Instruction Instruction <thinstruction< th=""> <thinstruction< th=""></thinstruction<></thinstruction<>	Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
High Level Output Voltage V _{OH} Ioh = -4 mA V _{DD1} , V _{DD2} - 0.4 3.1 V Low Level Output Voltage V _{OL} Iol = 4 mA 0.2 0.4 V Input Leakage Current IL ±10 µµ Output Impedance ¹ Z _O 85 0.2 Enable Input High Current I _{ENH} V _{ENx} = V _{IL} 2.0 µµ Enable Input Low Current I _{ENL} V _{ENx} = V _{IL} 2.0 µµ DC Supply Current (All inputs 0 vor at supply) Si8455Bx V _{DD1} All inputs 0 dc 2.3 3.5 m. V _{DD2} All inputs 0 dc 2.3 3.5 m. V _{DD1} All inputs 0 dc 4.5 6.8 m. V _{DD1} All inputs 1 dc 4.5 6.8 m. V _{DD1} All inputs 1 dc 4.5 6.8 m. V _{DD2} 3.5 5.3 5.3	High Level Input Voltage	V _{IH}		2.0			V
High Level Output Voltage V _{OH} Ioh = -4 mA V _{DD1} , V _{DD2} - 0.4 3.1 V Low Level Output Voltage V _{OL} Iol = 4 mA 0.2 0.4 V Input Leakage Current IL ±10 µµ Output Impedance ¹ Z _O 85 0.2 Enable Input High Current I _{ENH} V _{ENx} = V _{IL} 2.0 µµ Enable Input Low Current I _{ENL} V _{ENx} = V _{IL} 2.0 µµ DC Supply Current (All inputs 0 V or at supply) Si8455Bx V _{DD1} All inputs 0 dc 7.0 10.5 4.4 m. V _{DD2} All inputs 1 dc 7.0 10.5 6.8 6.8 6.8 6.8 6.8 6.8 6.8 6.8 6.5 m. 6.5 m.	Low Level Input Voltage	V _{IL}		—		0.8	V
Input Leakage Current IL ±10 µµ Output Impedance ¹ Z _O 85 Gr Enable Input High Current I _{ENH} V _{ENx} = V _{IH} 2.0 µµ Enable Input Low Current I _{ENL} V _{ENx} = V _{IL} 2.0 µµ DC Supply Current (All inputs 0 dc 1.6 2.4 µµ VDD1 All inputs 0 dc 7.0 10.5 <	High Level Output Voltage		loh = –4 mA	$V_{DD1}, V_{DD2} - 0.4$	3.1	_	V
Output Impedance ¹ Z _O 85 G. Enable Input High Current I _{ENH} V _{ENx} = V _{IL} - 2.0 µµ Enable Input Low Current I _{ENL} V _{ENx} = V _{IL} - 2.0 µµ DC Supply Current (All inputs 0 v or at supply) Si8455Bx V _{DD1} All inputs 0 dc 1.6 2.4 M V _{DD2} All inputs 0 dc 7.0 10.5 M	Low Level Output Voltage	V _{OL}	lol = 4 mA	—	0.2	0.4	V
Enable Input High Current IENH VENx = VIH - 2.0 - µµ Enable Input Low Current IENL VENx = VIL - 2.0 - µµ DC Supply Current (All inputs 0 dc - 1.6 2.4 µµ VDD1 All inputs 0 dc - 1.6 2.4 m. VDD2 All inputs 0 dc - 7.0 10.5 . . VDD1 All inputs 1 dc - 7.0 10.5 .	Input Leakage Current	ΙL		-	_	±10	μA
Enable Input Low Current I _{ENL} V _{ENx} = V _{IL} – 2.0 – µµ DC Supply Current (All inputs 0 V or at supply) Si8455Bx V _{DD1} All inputs 0 dc – 1.6 2.4 m. V _{DD2} All inputs 0 dc – 2.9 4.4 m. V _{DD2} All inputs 0 dc – 2.3 3.5 m. V _{DD1} All inputs 0 dc – 2.3 3.5 m. V _{DD2} All inputs 0 dc – 2.3 3.5 m. V _{DD1} All inputs 0 dc – 2.3 3.5 m. V _{DD2} All inputs 1 dc – 4.5 6.8 m. V _{DD2} All inputs 1 dc – 4.5 6.8 m. V _{DD1} All inputs 5 dot HZ square wave, CI = 15 pF on all outputs) m. 3.6 5.4 m. Si8455Bx – – 3.6 5.4 m. m. V _{DD1} – –	Output Impedance ¹	Z _O		—	85		Ω
DC Supply Current (All inputs 0 V or at supply) Si8455Bx All inputs 0 dc - 1.6 2.4 m. VDD1 All inputs 0 dc - 2.9 4.4 m. VD1 All inputs 1 dc - 7.0 10.5 VD1 All inputs 1 dc - 3.1 4.7 Si8442Bx All inputs 0 dc - 2.3 3.5 m. VD01 All inputs 1 dc - 2.3 3.5 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 500 kHz square wave, CI = 15 pF on all outputs) Si8455Bx m. 5.3 m. VD01 - - 3.6 5.4 m. m. VD01 - - 3.6 5.4 m. m. VD01	Enable Input High Current	I _{ENH}	V _{ENx} = V _{IH}	- 0	2.0	_	μA
Si8455Bx All inputs 0 dc - 1.6 2.4 m. VDD1 All inputs 0 dc - 2.9 4.4 m. VDD1 All inputs 1 dc - 7.0 10.5 m. Si8442Bx All inputs 0 dc - 3.1 4.7 Si8442Bx - 3.1 4.7 VDD1 All inputs 0 dc - 2.3 3.5 m. - 3.5 5.3 m. VDD2 All inputs 1 dc - 4.5 6.8 - 2.3 3.5 m. VDD1 All inputs 1 dc - 4.5 6.8 - - 4.5 6.8 - - 3.5 5.3 m. VDD2 All inputs 1 dc - 4.3 6.5 m. m. - 3.5 5.3 m. VDD2 - - 3.6 5.4 m. - 3.6 5.4 m. VDD1 - - 4.8 6	Enable Input Low Current	I _{ENL}	V _{ENx} = V _{IL}		2.0		μA
VDD1 All inputs 0 dc - 1.6 2.4 VD2 All inputs 0 dc - 2.9 4.4 m. VD01 All inputs 1 dc - 7.0 10.5 m. Si8442Bx All inputs 0 dc - 2.3 3.5 m. VD01 All inputs 0 dc - 2.3 3.5 m. VD01 All inputs 0 dc - 2.3 3.5 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 All inputs 1 dc - 4.5 6.8 m. VD01 - 4.3 6.5 m. m. VD1 - - 3.6 5.4 m. VD1 - 3.6 5.4 m. m. VD1 - 3.6 5.4 m. m. VD1 - 4.3 6.5 m.	D	C Supply C	urrent (All inputs 0	V or at supply)			
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1 Mbps Supply Current (All inputs = 500 kHz square wave, CI = 15 pF on all outputs) Si8455Bx — 4.3 6.5 m. VDD1 — 4.3 6.5 m. Si8455Bx — 3.5 5.3 m. Si8442Bx — 3.6 5.4 m. VDD1 — 3.6 5.4 m. VD2 — 3.6 5.4 m. Si8455Bx — 3.6 5.4 m. VD1 — 3.6 5.4 m. Si8455Bx — 4.3 6.5 m. VD1 — 4.3 6.5 m. VD1 — 4.3 6.5 m. VD2 — 4.8 6.7 m. Si845Bx — 4.2 5.9 m. VD2 — 4.2 5.9 m. VD2 — 4.2 5.9 m. VD2 — 4.2 </td <td></td> <td></td> <td></td> <td>—</td> <td></td> <td></td> <td></td>				—			
Si8455Bx — 4.3 6.5 m. V _{DD1} — 3.5 5.3 m. Si8442Bx — 3.6 5.4 m. V _{DD1} — 3.6 5.4 m. V _{DD2} — 3.6 5.4 m. Si8442Bx V _{DD1} — 3.6 5.4 m. Si8455Bx V _{DD1} — 4.3 6.5 m. V _{DD2} — 4.8 6.7 m. Si8442Bx V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. I00 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)				—			
VDD1 VDD2 4.3 3.5 6.5 5.3 m. Si8442Bx VDD1 VDD2 3.6 3.6 5.4 m. 10 Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs) 4.3 3.6 6.5 5.4 m. Si8455Bx VDD1 VDD2 4.3 4.8 6.5 6.7 m. Si8455Bx VDD1 VDD2 4.3 4.8 6.5 6.7 m. Si8442Bx VDD1 VDD2 4.2 5.9 5.9 m. Si8442Bx VDD1 VDD2 4.2 5.9 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs) 10 4.2 5.9		ent (All inpu	its = 500 kHz squar	e wave, CI = 15 pF	on all out	puts)	
VDD2 3.5 5.3 Si8442Bx 3.6 5.4 m. VDD1 3.6 5.4 m. VDD2 3.6 5.4 m. IO Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs) Si8455Bx 4.3 6.5 m. Si8455Bx VDD1 4.8 6.7 m. Si8442Bx 4.8 6.7 m. Si8442Bx 4.2 5.9 m. VDD1 4.2 5.9 m. VDD1 4.2 5.9 m. VD1 4.2 5.9 m. VD2 4.2 5.9 m. VD2 4.2 5.9 m. Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs) Supply Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)							
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VDD1 VDD2 3.6 5.4 m. 10 Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs) Si8455Bx VDD1 VDD2 4.3 6.5 m. Si8442Bx 4.8 6.7 m. VDD1 VDD2 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs) 4.2 5.9	V _{DD2}			—	3.5	5.3	
VDD1	Si8442Bx						
V _{DD2} — 3.6 5.4 10 Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs) Si8455Bx — 4.3 6.5 m. V _{DD1} — 4.8 6.7 m. Si8442Bx — 4.2 5.9 m. V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)	V _{DD1}			—	3.6	5.4	mA
10 Mbps Supply Current (All inputs = 5 MHz square wave, CI = 15 pF on all outputs) Si8455Bx — 4.3 6.5 m. V _{DD1} — 4.8 6.7 m. Si8442Bx — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. Si8442Bx — 4.2 5.9 m. V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m.				—	3.6	5.4	
V _{DD1} — 4.3 6.5 m. V _{DD2} — 4.8 6.7 m. Si8442Bx — 4.2 5.9 m. V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. IO0 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)		rrent (All inp	outs = 5 MHz squar	e wave, CI = 15 pF	on all out	outs)	
V _{DD2} — 4.8 6.7 Si8442Bx — 4.8 5.9 m. V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)	Si8455Bx						
VDD2 — 4.8 6.7 Si8442Bx — 4.8 5.9 m. VDD1 — 4.2 5.9 m. VDD2 — 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)					4.3	6.5	mA
Si8442Bx — 4.2 5.9 m. V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)	V						
V _{DD1} — 4.2 5.9 m. V _{DD2} — 4.2 5.9 m. 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)						0.1	
VDD2 — 4.2 5.9 100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)					10	FO	m^
100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)							IIIA
Notes:	100 Mbps Supply Cu	rrent (All inp	outs = 50 MHz squa	are wave, $CI = 15 p$	F on all ou	tputs)	
1. The nominal output impedance of an isolator driver channel is approximately 85 Ω , ±40%, which is a combination of the second se	Notes:						

where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces.
 tracking points the magnitude of the difference in propagation delay times measured between different units operating.

2. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

3. Start-up time is the time period from the application of power to valid data at the output.

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Table 4. Electrical Characteristics (Continued)

(V_{DD1} = 3.3 V±10%, V_{DD2} = 3.3 V±10%, T_A = -40 to 125 °C)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
Si8455Bx						
V _{DD1}				4.4	6.6	mA
V _{DD2}			—	16.8	21	
Si8442Bx						
V _{DD1}				8.6	10.8	mA
V _{DD2}			_	8.6	10.8	
	Tir	ning Characteristi	cs			
Si845xBx, Si8442Bx						
Maximum Data Rate			0	—	1.0	Mbps
Minimum Pulse Width				_	250	ns
Propagation Delay	t _{PHL} ,t _{PLH}	See Figure 2			35	ns
Pulse Width Distortion	PWD	See Figure 2			25	ns
t _{PLH} - t _{PHL}						_
Propagation Delay Skew ²	t _{PSK(P-P)}			—	40	ns
Channel-Channel Skew	t _{PSK}		_) –	35	ns
Si845xBx, Si8442Bx			5			
Maximum Data Rate			0	_	150	Mbps
Minimum Pulse Width			_	—	6.0	ns
Propagation Delay	t _{PHL} , t _{PLH}	See Figure 2	3.0	6.0	9.5	ns
Pulse Width Distortion	PWD	See Figure 2	_	1.5	2.5	ns
t _{PLH} - t _{PHL}						
Propagation Delay Skew ²	t _{PSK(P-P)}		—	2.0	3.0	ns
Channel-Channel Skew	t _{PSK}			0.5	1.8	ns
All Models						
Output Rise Time	t _r	C _L = 15 pF	—	4.3	6.1	ns
		See Figure 2				
Output Fall Time	t _f	C _L = 15 pF	—	3.0	4.3	ns
A 10 - 10 - 10 - 10 - 10 - 10 - 10 - 10		See Figure 2				
Common Mode Transient Immunity	CMTI	$V_{I} = V_{DD} \text{ or } 0 \text{ V}$		25	_	kV/µs
Enable to Data Valid	t _{en1}	See Figure 1		5.0	8.0	ns
Enable to Data Tri-State	t _{en2}	See Figure 1		7.0	9.2	ns
Start-up Time ³	t _{SU}			15	40	μs
Notes:	-50					~~~

Notes:

The nominal output impedance of an isolator driver channel is approximately 85 Ω, ±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces.

2. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

3. Start-up time is the time period from the application of power to valid data at the output.

Si844x/5x QSOP

Table 5. Electrical Characteristics¹

(V_{DD1} = 2.70 V, V_{DD2} = 2.70 V, T_A = –40 to 125 °C)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
High Level Input Voltage	V _{IH}		2.0	_		V
Low Level Input Voltage	V _{IL}		—	_	0.8	V
High Level Output Voltage	V _{OH}	loh = –4 mA	$V_{DD1}, V_{DD2} - 0.4$	2.3	—	V
Low Level Output Voltage	V _{OL}	lol = 4 mA	—	0.2	0.4	V
Input Leakage Current	١L		—	—	±10	μA
Output Impedance ²	Z _O		-	85	—	Ω
Enable Input High Current	I _{ENH}	V _{ENx} = V _{IH}	-	2.0	—	μA
Enable Input Low Current	I _{ENL}	$V_{ENx} = V_{IL}$	- 7	2.0	—	μA
[C Supply C	current (All inputs 0	V or at supply)			
Si8455Bx V _{DD1} V _{DD2} V _{DD1} V _{DD2}		All inputs 0 DC All inputs 0 DC All inputs 1 DC All inputs 1 DC		1.6 2.9 7.0 3.1	2.4 4.4 10.5 4.7	mA
Si8442Bx V _{DD1} V _{DD2} V _{DD1} V _{DD2}		All inputs 0 DC All inputs 0 DC All inputs 1 DC All inputs 1 DC	8-	2.3 2.3 4.5 4.5	3.5 3.5 6.8 6.8	mA
1 Mbps Supply Cu	rent (All inp	uts = 500 kHz squar	e wave, CI = 15 pF	on all outp	outs)	•
Si8455Bx V _{DD1} V _{DD2}	20	CN		4.3 3.5	6.5 5.3	mA
Si8442Bx V _{DD1} V _{DD2}		puts = 5 MHz square	— — —	3.6 3.6	5.4 5.4	mA
		iputs – 5 Militz square	e wave, CI – 15 pr			
Si8455Bx V _{DD1} V _{DD2}				4.3 4.8	6.5 6.7	mA
Si8442Bx V _{DD1} V _{DD2}				4.2 4.2	5.9 5.9	mA
 Notes: Specifications in this table are constrained to T_A = 0 to 85 °C. The nominal output impedance value of the on-chip series terr where transmission line effects 	of an isolato nination resis	r driver channel is appr tor and channel resista	oximately 85 Ω , ±40% nce of the output driv	%, which is a rer FET. Wh	a combinatio en driving lo	n of the

impedance PCB traces. **3.** $t_{PSK(P-P)}$ is the magnitude of the difference in propagation delay times measured between different units operating at the

same supply voltages, load, and ambient temperature.4. Start-up time is the time period from the application of power to valid data at the output.

Table 5. Electrical Characteristics¹ (Continued) (V_{DD1} = 2.70 V, V_{DD2} = 2.70 V, T_A = -40 to 125 °C)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit			
100 Mbps Supply Current (All inputs = 50 MHz square wave, CI = 15 pF on all outputs)									
Si8455Bx									
V _{DD1}			—	4.3	6.5	mA			
V _{DD2}				13.3	16.6				
Si8442Bx									
V _{DD1}				7.2	9.0	mA			
V _{DD2}			—	7.2	9.0				
	Ti	ming Characteristi	cs						
Si845xBx, Si8442Bx									
Maximum Data Rate			0	—	1.0	Mbps			
Minimum Pulse Width			\leftarrow	G	250	ns			
Propagation Delay	t _{PHL} ,t _{PLH}	See Figure 2	-		35	ns			
Pulse Width Distortion	PWD	See Figure 2		—	25	ns			
t _{PLH} – t _{PHL}									
Propagation Delay Skew ³	t _{PSK(P-P)}			- 1	40	ns			
Channel-Channel Skew	t _{PSK}	N.	5	—	35	ns			
Si845xBx, Si8442Bx									
Maximum Data Rate			0	_	150	Mbps			
Minimum Pulse Width			-		6.0	ns			
Propagation Delay	t _{PHL} , t _{PLH}	See Figure 2	3.0	6.0	9.5	ns			
Pulse Width Distortion	PWD	See Figure 2	—	1.5	2.5	ns			
t _{PLH} – t _{PHL}									
Propagation Delay Skew ³	t _{PSK(P-P)}		—	2.0	3.0	ns			
Channel-Channel Skew	t _{PSK}		—	0.5	1.8	ns			
Notes:			I						

otes:

1. Specifications in this table are also valid at VDD1 = 2.6 V and VDD2 = 2.6 V when the operating temperature range is constrained to $T_A = 0$ to 85 °C.

2. The nominal output impedance of an isolator driver channel is approximately 85 Ω , ±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces.

3. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

4. Start-up time is the time period from the application of power to valid data at the output.

Table 5. Electrical Characteristics¹ (Continued)

 $(V_{DD1} = 2.70 \text{ V}, V_{DD2} = 2.70 \text{ V}, T_A = -40 \text{ to } 125 \text{ °C})$

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
All Models		<u> </u>	ł	!	!	
Output Rise Time	t _r	C _L = 15 pF See Figure 2		4.8	6.5	ns
Output Fall Time	t _f	C _L = 15 pF See Figure 2		3.2	4.6	ns
Common Mode Transient Immunity	CMTI	$V_{I} = V_{DD} \text{ or } 0 \text{ V}$	_	25	—	kV/µs
Enable to Data Valid	t _{en1}	See Figure 1	-	5.0	8.0	ns
Enable to Data Tri-State	t _{en2}	See Figure 1	- 7	7.0	9.2	ns
Start-up Time ⁴	t _{SU}			15	40	μs

Notes:

1. Specifications in this table are also valid at VDD1 = 2.6 V and VDD2 = 2.6 V when the operating temperature range is constrained to $T_A = 0$ to 85 °C.

2. The nominal output impedance of an isolator driver channel is approximately 85 Ω, ±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces.

3. t_{PSK(P-P)} is the magnitude of the difference in propagation delay times measured between different units operating at the same supply voltages, load, and ambient temperature.

4. Start-up time is the time period from the application of power to valid data at the output.

Table 6. Regulatory Information*

CSA

The Si84xx is certified under CSA Component Acceptance Notice 5A. For more details, see File 232873. **VDE**

VDE

The Si84xx is certified according to IEC 60747-5-2. For more details, see File 5006301-4880-0001.

60747-5-2: Up to 560 V_{peak} for basic insulation working voltage.

UL

The Si84xx is certified under UL1577 component recognition program. For more details, see File E257455.

*Note: Regulatory Certifications apply to 1.0 kV_{RMS} rated devices which are production tested to 1.2 kV_{RMS} for 1 sec. For more information, see "5. Ordering Guide" on page 25.

Parameter	Symbol	Test Condition	Value	Unit
Farameter	Symbol	Test condition	QSOP-16	Unit
Nominal Air Gap (Clearance)	L(IO1)		3.6	mm
Nominal External Tracking (Creepage)	L(IO2)		3.6	mm
Minimum Internal Gap (Internal Clearance)			0.008	mm
Tracking Resistance (Proof Tracking Index)	PTI	IEC 60112	600	V _{RMS}
Erosion Depth	ED		0.031	mm
Resistance (Input-Output) ¹	R _{IO}		10 ¹²	Ω
Capacitance (Input-Output) ¹	C _{IO}	f = 1 MHz	2.0	pF
Input Capacitance ²	Cl		4.0	pF
Neteo	·			

Notes:

1. To determine resistance and capacitance, the Si84xx is converted into a 2-terminal device. Pins 1–8 are shorted together to form the first terminal and pins 9–16 are shorted together to form the second terminal. The parameters are then measured between these two terminals.

2. Measured from input pin to ground.

Table 8. IEC 60664-1 (VDE 0844 Part 2) Ratings

Parameter	Test Condition	Specification
Basic Isolation Group	Material Group	I
Installation Classification	Rated Mains Voltages ≤ 150 V _{RMS}	I-IV
	Rated Mains Voltages ≤ 300 V _{RMS}	1-111
	Rated Mains Voltages ≤ 400 V _{RMS}	I-II
	Rated Mains Voltages ≤ 600 V _{RMS}	I-II

Table 9. IEC 60747-5-2 Insulation Characteristics for Si84xxxB*

Parameter	Symbol	Test Condition	Characteristic	Unit		
Maximum Working Insulation Voltage	V _{IORM}		560	V peak		
Input to Output Test Voltage	V _{PR}	Method b1 (V _{IORM} x 1.875 = V _{PR} , 100% Production Test, t _m = 1 sec, Partial Discharge < 5 pC)	1050	V peak		
Transient Overvoltage	V _{IOTM}	t = 60 sec	4000	V peak		
Pollution Degree (DIN VDE 0110, Table 1)			2			
Insulation Resistance at T_S , V_{IO} = 500 V	R _S	. 0.	>10 ⁹	Ω		
*Note: Maintenance of the safety data is ensured by protective circuits. The Si84xx provides a climate classification of 40/125/21.						

Table 10. Safety Limiting Values¹

			•	C	Ma		
Parameter	Symbol	Test Condition	Min	Тур	Si844x QSOP-16	Si845x QSOP-16	Unit
Case Temperature	Τ _S			_	150	150	°C
Safety input, output, or supply current	۱ _S	θ _{JA} = 105 °C/W (QSOP-16), V _I = 5.5 V, T _J = 150 °C, T _A = 25 °C			210	215	mA
Device Power Dissipa- tion ²	P _D		_	_	275	415	mW

Notes:

1. Maximum value allowed in the event of a failure; also see the thermal derating curve in Figures 3 and 4.

2. The Si84xx is tested with VDD1 = VDD2 = 5.5 V, TJ = 150 °C, CL = 15 pF, input a 150 Mbps 50% duty cycle square wave.

Table 1 ^r	1. Therma	I Characteristics
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Parameter	Symbol	Si84xx QSOP-16	Unit
IC Junction-to-Air Thermal Resistance	θ_{JA}	105	°C/W

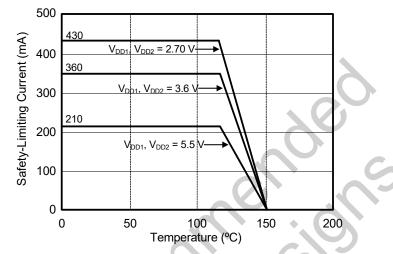


Figure 3. (Si844x, QSOP-16) Thermal Derating Curve, Dependence of Safety Limiting Values with Case Temperature per DIN EN 60747-5-2

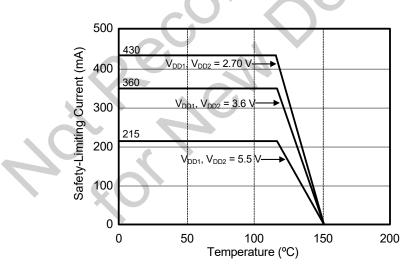


Figure 4. (Si845x, QSOP-16) Thermal Derating Curve, Dependence of Safety Limiting Values with Case Temperature per DIN EN 60747-5-2

2. Functional Description

2.1. Theory of Operation

The operation of an Si84xx channel is analogous to that of an opto coupler, except an RF carrier is modulated instead of light. This simple architecture provides a robust isolated data path and requires no special considerations or initialization at start-up. A simplified block diagram for a single Si84xx channel is shown in Figure 5.

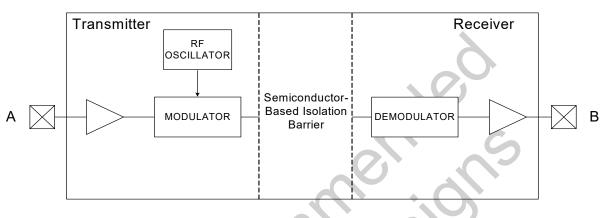


Figure 5. Simplified Channel Diagram

A channel consists of an RF Transmitter and RF Receiver separated by a semiconductor-based isolation barrier. Referring to the Transmitter, input A modulates the carrier provided by an RF oscillator using on/off keying. The Receiver contains a demodulator that decodes the input state according to its RF energy content and applies the result to output B via the output driver. This RF on/off keying scheme is superior to pulse code schemes as it provides best-in-class noise immunity, low power consumption, and better immunity to magnetic fields. See Figure 6 for more details.

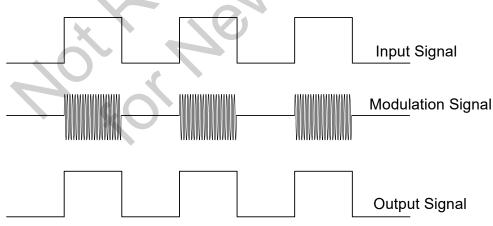
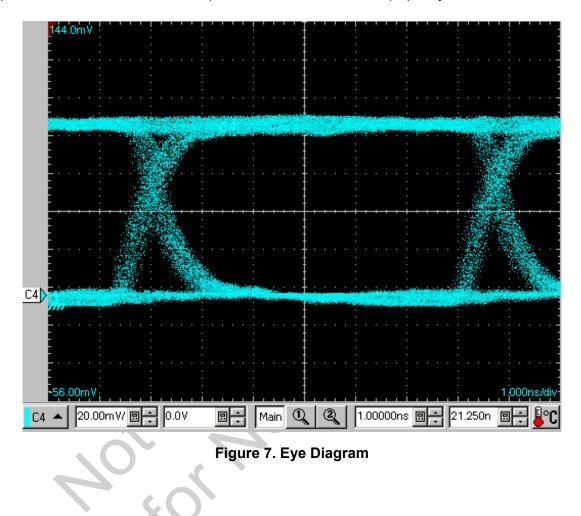


Figure 6. Modulation Scheme

2.2. Eye Diagram

Figure 7 illustrates an eye-diagram taken on an Si8455. For the data source, the test used an Anritsu (MP1763C) Pulse Pattern Generator set to 1000 ns/div. The output of the generator's clock and data from an Si8455 were captured on an oscilloscope. The results illustrate that data integrity was maintained even at the high data rate of 150 Mbps. The results also show that 2 ns pulse width distortion and 250 ps peak jitter were exhibited.



2.3. Device Operation

Device behavior during start-up, normal operation, and shutdown is shown in Table 12. Table 13 provides an overview of the output states when the Enable pins are active.

V _I Input ^{1,2}	EN Input ^{1,2,3}	VDDI State ^{1,4,5}	VDDO State ^{1,4,5}	V _O Output ^{1,2}	Comments
Н	H or NC	Р	Р	Н	Enabled, normal operation.
L	H or NC	Р	Р	L	
X ⁶	L	Р	Р	Hi-Z ⁷	Disabled.
X ⁶	H or NC	UP	Р	L	Upon transition of VDDI from unpowered to powered, V_O returns to the same state as V_I in less than 1 $\mu s.$
X ⁶	L	UP	Р	Hi-Z ⁷	Disabled.
X ⁶	X ⁶	Р	UP	Undetermined	Upon transition of VDDO from unpowered to powered, V _O returns to the same state as V _I within 1 μ s, if EN is in either the H or NC state. Upon transition of VDDO from unpowered to powered, V _O returns to Hi-Z within 1 μ s if EN is L.

Table 12. Si84xx Logic Operation Table

Notes:

1. VDDI and VDDO are the input and output power supplies. V_I and V_O are the respective input and output terminals. EN is the enable control input located on the same output side.

2. X = not applicable; H = Logic High; L = Logic Low; Hi-Z = High Impedance.

3. It is recommended that the enable inputs be connected to an external logic high or low level when the Si84xx is operating in noisy environments.

4. "Powered" state (P) is defined as 2.70 V < VDD < 5.5 V.

5. "Unpowered" state (UP) is defined as VDD = 0 V.

6. Note that an I/O can power the die for a given side through an internal diode if its source has adequate current.

7. When using the enable pin (EN) function, the output pin state goes into a high-impedance state when the EN pin is disabled (EN = 0).

P/N	EN1 ^{1,2}	EN2 ^{1,2}	Operation	
Si8442	Н	Х	Outputs A3 and A4 are enabled and follow input state.	
	L	Х	Outputs A3 and A4 are disabled and Logic Low or in high impedance state. ³	
	Х	Н	Dutputs B1 and B2 are enabled and follow input state.	
	Х	L	Outputs B1 and B2 are disabled and Logic Low or in high impedance state. ³	
Si8455	—	_	Outputs B1, B2, B3, B4, B5 are enabled and follow input state.	

Table 13. Enable Input Truth Table¹

Notes:

Enable inputs EN1 and EN2 can be used for multiplexing, for clock sync, or other output control. These inputs are
internally pulled-up to local VDD by a 3 µA current source allowing them to be connected to an external logic level (high
or low) or left floating. To minimize noise coupling, do not connect circuit traces to EN1 or EN2 if they are left floating. If
EN1, EN2 are unused, it is recommended they be connected to an external logic level, especially if the Si845x is
operating in a noisy environment.

- **2.** X = not applicable; H = Logic High; L = Logic Low.
- 3. When using the enable pin (EN) function, the output pin state goes into a high-impedance state when the EN pin is disabled (EN = 0).

- Aem

2.4. Layout Recommendations

To ensure safety in the end user application, high voltage circuits (i.e., circuits with >30 V_{AC}) must be physically separated from the safety extra-low voltage circuits (SELV is a circuit with <30 V_{AC}) by a certain distance (creepage/clearance). If a component, such as a digital isolator, straddles this isolation barrier, it must meet those creepage/clearance requirements and also provide a sufficiently large high-voltage breakdown protection rating (commonly referred to as working voltage protection). Refer to the end-system specification (61010-1, 60950-1, etc.) requirements before starting any design that uses a digital isolator.

The following sections detail the recommended bypass and decoupling components necessary to ensure robust overall performance and reliability for systems using the Si84xx digital isolators.

2.4.1. Supply Bypass

Digital integrated circuit components typically require 0.1 μ F (100 nF) bypass capacitors when used in electrically quiet environments. However, digital isolators are commonly used in hazardous environments with excessively noisy power supplies. To counteract these harsh conditions, it is recommended that an additional 1 μ F bypass capacitor be added between VDD and GND on both sides of the package. The capacitors should be placed as close as possible to the package to minimize stray inductance. If the system is excessively noisy, it is recommended that the designer add 50 to 100 Ω resistors in series with the VDD supply voltage source and 50 to 300 Ω resistors in series with the digital inputs/outputs (see Figure 8). For more details, see "3. Errata and Design Migration Guidelines" on page 23.

All components upstream or downstream of the isolator should be properly decoupled as well. If these components are not properly decoupled, their supply noise can couple to the isolator inputs and outputs, potentially causing damage if spikes exceed the maximum ratings of the isolator (6 V). In this case, the 50 to 300 Ω resistors protect the isolator's inputs/outputs (note that permanent device damage may occur if the absolute maximum ratings are exceeded). Functional operation should be restricted to the conditions specified in Table 1, "Recommended Operating Conditions," on page 4.

2.4.2. Pin Connections

No connect pins are not internally connected. They can be left floating, tied to V_{DD}, or tied to GND.

2.4.3. Output Pin Termination

The nominal output impedance of an isolator driver channel is approximately 85 Ω , ±40%, which is a combination of the value of the on-chip series termination resistor and channel resistance of the output driver FET. When driving loads where transmission line effects will be a factor, output pins should be appropriately terminated with controlled impedance PCB traces. The series termination resistor values should be scaled appropriately while keeping in mind the recommendations described in "2.4.1. Supply Bypass" above.

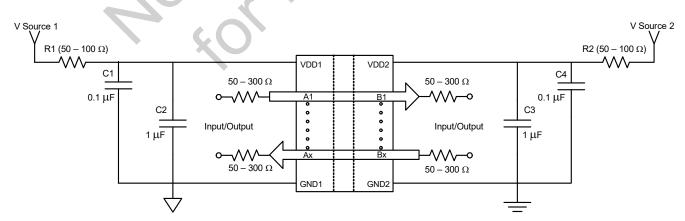
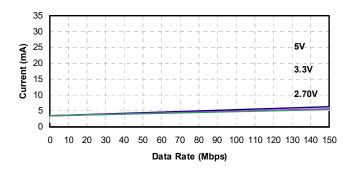
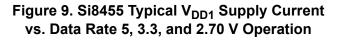


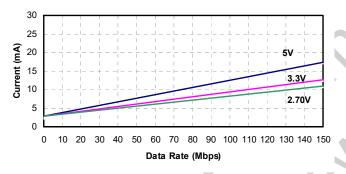
Figure 8. Recommended Bypass Components for the Si84xx Digital Isolator Family

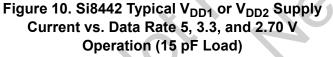
2.5. Typical Performance Characteristics

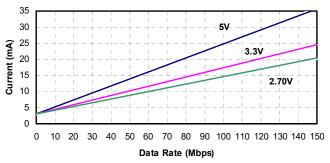
The typical performance characteristics depicted in the following diagrams are for information purposes only. Refer to Tables 3, 4, and 5 for actual specification limits.

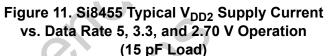


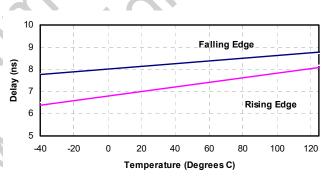


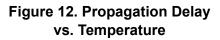




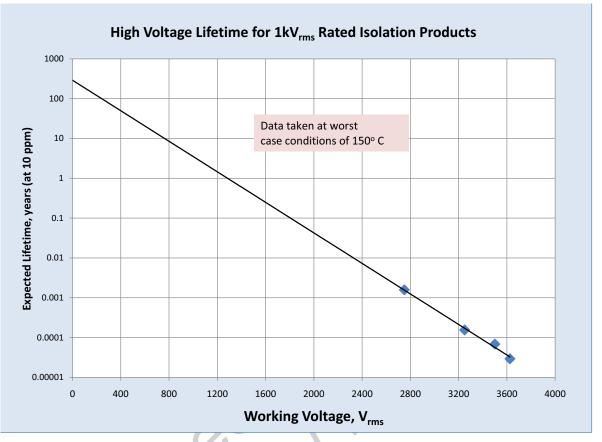


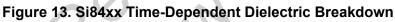






Si844x/5x QSOP





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3. Errata and Design Migration Guidelines

No errata exist for Revision D. However, the following recommendations apply to Revision D devices. See "5. Ordering Guide" on page 25 for more details.

3.1. Power Supply Bypass Capacitors (Revision C and Revision D)

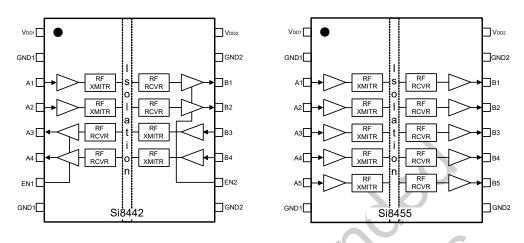
When using the Si844x isolators with power supplies \geq 4.5 V, sufficient VDD bypass capacitors must be present on both the VDD1 and VDD2 pins to ensure the VDD rise time is less than 0.5 V/µs (which is > 9 µs for a \geq 4.5 V supply). Although rise time is power supply dependent, \geq 1 µF capacitors are required on both power supply pins (VDD1, VDD2) of the isolator device.

3.1.1. Resolution

For recommendations on resolving this issue, see "2.4.1. Supply Bypass" on page 20. Additionally, refer to "5. Ordering Guide" on page 25 for current ordering information.

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4. Pin Descriptions



Name	SOIC-16 Pin#	Туре	Description (Si8442)	Description (Si8455)
V _{DD1}	1	Supply	Side 1 power supply	Side 1 power supply
GND1	2	Ground	Side 1 ground	Side 1 ground
A1	3	Digital Input	Side 1 digital input	Side 1 digital input
A2	4	Digital Input	Side 1 digital input	Side 1 digital input
A3	5	Digital I/O	Side 1 digital output	Side 1 digital input
A4	6	Digital I/O	Side 1 digital output	Side 1 digital input
A5/EN1	7	Digital Input	Side 1 active high enable	Side 1 digital input
GND1	8	Ground	Side 1 ground	Side 1 ground
GND2	9	Ground	Side 2 ground	Side 2 ground
B5/EN2	10	Digital Input or Enable	Side 2 active high enable	Side 2 digital output
B4	11	Digital I/O	Side 2 digital input	Side 2 digital output
B3	12	Digital I/O	Side 2 digital input	Side 2 digital output
B2	13	Digital Output	Side 2 digital output	Side 2 digital output
B1	14	Digital Output	Side 2 digital output	Side 2 digital output
GND2	15	Ground	Side 2 ground	Side 2 ground
V _{DD2}	16	Supply	Side 2 power supply	Side 2 power supply

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5. Ordering Guide

These devices are not recommended for new designs. Please see the Si864x or Si865x datasheet for replacement options.

Ordering Part Number (OPN)	Alternative Part Number (APN)	Number of Inputs VDD1 Side	Number of Inputs VDD2 Side	Maximum Data Rate (Mbps)	Isolation Rating	Package Type
Si8442BA-D-IU	Si8642BA-C-IU	2	2	150	1 kVrms	QSOP-16
Si8455BA-B-IU	Si8655BA-C-IU	5	0	150	1 kVrms	Q30F-10
*Note: All packages ar	e RoHS-compliant M	Ioisture sensitivity	v level is MSI 24 w	vith neak reflow t	emperature of 2	260 °C according to

Table 14. Ordering Guide for Valid OPNs*

Note: All packages are RoHS-compliant. Moisture sensitivity level is MSL2A with peak reflow temperature of 260 °C according to the JEDEC industry standard classifications and peak solder temperature.

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6. Package Outline: 16-Pin QSOP

Figure 14 illustrates the package details for the Si84xx in a 16-pin QSOP package. Table 15 lists the values for the dimensions shown in the illustration.

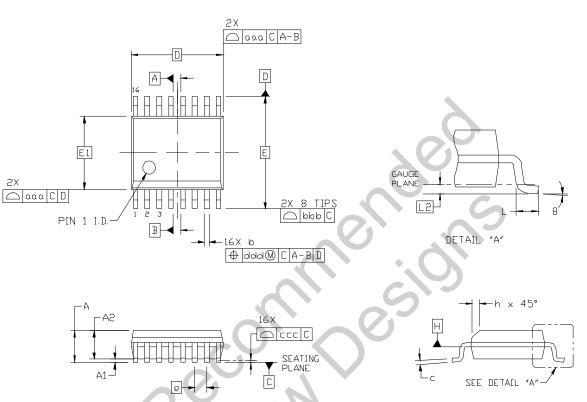


Figure 14. 16-pin QSOP Package

Dimension	Min	Max	
A	— 1.75		
A1	0.10	0.25	
A2	1.25	—	
b	0.20	0.30	
с	0.17	0.25	
D	4.89 BSC		
E	6.00 E	BSC	
E1	3.90 E	BSC	
е	0.635	BSC	
L	0.40	1.27	
L2	0.25 BSC		
h	0.25	0.50	

Table 15. Package Diagram Dimensions

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Dimension	Min	Мах			
θ	0°	8°			
aaa	0.10				
bbb	0.20				
CCC	0.10				
ddd	0.25				
 Notes: 1. All dimensions shown are in millimeters (mm) unless otherwise noted. 2. Dimensioning and Tolerancing per ANSI Y14.5M-1994. 					

Table 15. Package Diagram Dimensions (Continued)

3. This drawing conforms to the JEDEC Solid State Outline MO-137, Variation AB.

4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification

for Small Body Components.

7. Land Pattern: 16-Pin QSOP

Figure 15 illustrates the recommended land pattern details for the Si84xx in a 16-pin QSOP. Table 16 lists the values for the dimensions shown in the illustration.

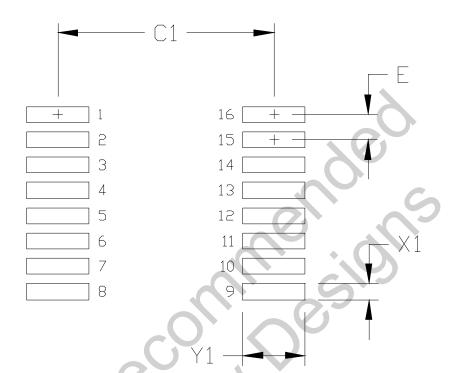


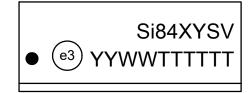
Figure 15. 16-Pin QSOP PCB Land Pattern

Table 16. 16-Pin QSOP Land Pattern Dimensions

Dimension	Feature	(mm)		
C1	Pad Column Spacing	5.40		
E	Pad Row Pitch	0.635		
X1	Pad Width	0.40		
Y1	Pad Length	1.55		
 Notes: 1. This Land Pattern Design is based on IPC-7351 pattern SOP63P602X173-16N for Density Level B (Median Land Protrusion). 2. All feature sizes shown are at Maximum Material Condition (MMC) and a card fabrication tolerance of 0.05 mm is assumed. 				

8. Top Marking: 16-Pin QSOP

8.1. 16-Pin QSOP Top Marking



8.2. Top Marking Explanation

Line 1 Marking:	Base Part Number	Si84 = Isolator product series
	Ordering Options	XY = Channel Configuration
		X = # of data channels (5, 4)
	(See Ordering Guide for more	Y = # of reverse channels (2, 0)*
	information).	S = Speed Grade
		A = 1 Mbps; B = 150 Mbps
		V = Insulation rating
		A = 1 kV
Line 2 Marking:	Circle = 1.2 mm Diameter	"e3" Pb-Free Symbol
	YY = Year	Assigned by the assembly subcontractor. Corresponds
	WW = Work Week	to the year and work week of the mold date.
	TTTTTT = Mfg code	Manufacturing code from assembly purchase order
		form.
	Circle = 1.2 mm diameter	"e3" Pb-Free Symbol.
*Note: Si8455 has 0 r	everse channels	

*Note: Si8455 has 0 reverse channels.

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DOCUMENT CHANGE LIST

Revision 0.1 to Revision 1.0

- Changed document name from Si84x/5x QSOP to Si844x/5x QSOP.
- Updated " Features" on page 1.
- Moved Tables 1 and 2 to page 4.
- Updated Tables 6, 7, 8, and 9.
- Updated Table 12 footnotes.
- Added Figure 13, "Si84xx Time-Dependent Dielectric Breakdown," on page 22.

Revision 1.0 to Revision 1.1

- Deleted all references to 2.5 kV_{RMS}
- Updated Table 6, "Regulatory Information*," on page 12.
- Updated Figure 13, "Si84xx Time-Dependent Dielectric Breakdown," on page 22.
- Updated "2.4.1. Supply Bypass" on page 20.
- Added Figure 8, "Recommended Bypass Components for the Si84xx Digital Isolator Family," on page 20.
- Updated "3.1. Power Supply Bypass Capacitors (Revision C and Revision D)" on page 23.

Revision 1.1 to Revision 1.2

 Updated "5. Ordering Guide" on page 25 to include new title note and " Alternative Part Number (APN)" column.









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